

High Magnetic Field Sensor Using LaSb₂

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The magnetotransport properties of single crystals of the highly anisotropic layered metal LaSb₂ are reported in magnetic fields up to 45 T with fields oriented both parallel and perpendicular to the layers. Below 10 K the perpendicular magnetoresistance of LaSb₂ becomes temperature independent and is characterized by a 100-fold linear increase in resistance between 0 and 45 T with no evidence of quantum oscillations down to 50 mK. The Hall resistivity is hole-like and gives a high field carrier density of $n = 3 \times 10^{20} \text{ cm}^{-3}$. The feasibility of using LaSb₂ for magnetic field sensors is discussed.

One of the most successful strategies for producing technologically relevant magnetoresistive materials is to enhance the effects of field-dependent magnetic scattering processes through the creation of magnetic superlattices [1] or by doping magnetic insulators such that a magnetic and metal-insulator transition coincide [2]. Unexpectedly, there have been several recent discoveries of a large, non-saturating magnetoresistance (MR) in low carrier density non-magnetic metals [3, 4, 5, 6, 7] and semiconductors [8]. One class of these systems, the slightly off-stoichiometric silver chalcogenides, Ag_{2+Te} and Ag_{2+Se}, have shown significant promise as the basis of ultra-high magnetic field sensors by virtue of the fact that they exhibit a multi-fold, quasi-linear MR that remains unsaturated up to 60 T [8]. In this Letter we present magnetotransport data on the highly layered non-magnetic metal LaSb₂ which displays a 100-fold, linear MR with no sign of saturation up to 45 T. We show that in many respects, including sensitivity, linearity, synthesis characteristics and intrinsic anisotropy, LaSb₂ is a compelling candidate for high-field sensor development.

LaSb₂ is a member of the RSb₂ (R = La-Nd, Sm) family of compounds that all form in the orthorhombic SmSb₂ structure [9, 10]. LaSb₂, in particular, is comprised of alternating La/Sb layers and two-dimensional rectangular sheets of Sb atoms stacked along the c-axis [11]. Similar structural characteristics give rise to the anisotropic physical properties observed in all the compounds in the RSb₂ series [12]. Since LaSb₂ is non-magnetic, its low-temperature transport properties are not complicated by magnetic phase transitions which occur in the other members of this series [12].

Single crystals of LaSb₂ were grown from high purity La and Sb by the metallic flux method [13]. The orthorhombic SmSb₂-structure type was confirmed by single crystal X-ray diffraction. The crystals grow as large flat layered plates which are malleable and easily cleaved. Typically flux grown samples had dimensions of 5 mm x 5 mm x 0.2 mm. Electrical contact was made using Epotek [14] silver epoxy and 1 mil gold wire. Transport properties were measured using a 27 Hz 4-probe AC technique at temperatures from 0.03 - 300 K and in magnetic fields up to 45 T. In all of the measurements presented probe currents of 1 - 5 mA were used with corresponding power levels less than 10 nW. Hall effect measurements were made on natural thickness samples in a 4-wire geometry with data being taken in both positive and negative fields up to 30 T.

The in-plane zero-field electrical resistivity, ρ , of single crystals of LaSb₂ was measured from 1.8-300 K and found to be metallic ($d\rho/dT > 0$). The residual resistivity ratio (RRR) was large ($\rho_{ab}(300\text{K})/\rho_{ab}(2\text{K}) = 70-90$), indicating a high sample quality. In the main panel of Fig. 1 we show the transverse MR with the field oriented parallel and perpendicular to the ab-plane. Both MR's are positive and nearly linear above 2 T. Note the extreme anisotropy in the magnetotransport with the perpendicular MR being an order of magnitude larger than the parallel MR. The perpendicular MR was large, with resistance increasing by a factor of 90 from 0 to 45 T. The MR was temperature

independent below 10 K but decreased rapidly above 30 K. Interestingly, there is no evidence of saturation or quantum oscillations in the MR of Fig. 1 which has obvious advantages for magnetic field sensor applications. The solid lines in Fig. 1 are least-square fits to a fourth-order polynomial (Table 1). Note the high quality of the fits to the MR using this simple functional form. The relative field sensitivity, which is the figure of merit for a sensor, is represented by $\alpha = 1.23 \text{ T}^{-1}$. This sensitivity is roughly a factor of 4 greater than that of Ag_2Se (triangle symbols in Fig. 1).

The anisotropy of the MR can be demonstrated by measuring the transverse MR as a function of the tilt angle in a constant magnetic field. In Fig. 2 we plot the resistivity normalized by the parallel field value, ($H_z = 0$), as a function of the perpendicular component of the field H_x . Interestingly, the general shape of the MR curves in Fig. 2 is quite similar to those of Fig. 1. The solid lines are polynomial fits to the data (Table 1). In terms of a magnetic field sensor, this anisotropy can be exploited to determine the angle of orientation in tilted field studies. The micaceous nature of LaSb_2 not only produces an anisotropic MR but also presents a convenient geometry for Hall measurements, namely large flat crystals. In the main panel of Fig. 3 we plot the Hall resistivity, ρ_{xy} , as a function of magnetic field at $T = 2 \text{ K}$. In the right inset of Fig. 3 we show the low field behavior of ρ_{xy} which is negative below 0.5 T but becomes positive at higher fields. This latter behavior is often characteristic of a two-carrier system [18]. In the high field limit the majority carrier dominates, which in our case is hole-like. Above 10 T the Hall constant is $R_H = 2 \times 10^6 \text{ cm}^3/\text{T}$ which corresponds to a carrier density of $n = 3 \times 10^{20} \text{ cm}^{-3}$ and a Hall mobility $\mu_H = 0.05 \text{ m}^2/\text{Vs}$. We note that the overall shape of the Hall resistance curve in the right inset of Fig. 3, with its local minimum, is very similar in character to that of NbSe_2 and TaSe_2 which also form in non-magnetic micaceous crystalline structures [15].

A useful measure of the magnitude of the linear MR is the dimensionless Kohler slope, $S = (1/R_H)(dH) = dH$. Combining the Hall constant measurements with the value of α , obtained from the MR of Fig. 1, we get a high field value $S = 0.6$. This value is an order of magnitude larger than what is typical of other non-magnetic systems displaying a linear MR. Classically, the MR should vary quadratically with field. In a closed orbit system the MR saturates in the high field limit limit, $\omega_c \tau \ll 1$, where ω_c is the cyclotron frequency and τ is the elastic scattering time [18]. Over the past 30 years several mechanisms have been proposed to account for anomalous linear MR observed in a wide variety of non-magnetic systems such as elemental metals [5, 19], two-dimensional heterostructures [20], and disordered semiconductors [8]. Theories accounting for linear MR fall into two main categories. The first contains theories associated with the alteration of the structural symmetry due to the formation of a charge density wave (CDW) [21]. Linear MR in very pure elemental metals has been attributed to quantum fluctuations about a CDW ground state [16] and/or a magnetic breakdown of the CDW gap [15, 17]. The second includes theories which invoke high field quantization effects or singular scattering mechanisms which cannot be accounted for by the standard perturbative scattering formulations [3, 22]. Interestingly, the transition metal dichalcogenides NbSe_2 and TaSe_2 both have well established CDW ground states and exhibit an anomalous linear MR. These compounds are similar in structure to LaSb_2 , suggesting that perhaps a CDW state plays a central role in the MR of LaSb_2 . At this time, however, it is not known whether LaSb_2 undergoes a charge density wave transition.

It has been known for many years that the relative MR, ρ_{xy}/ρ_{xx} , of many metals and semimetals is a temperature independent function of magnetic field [23]. In particular, $\rho_{xy}/\rho_{xx} = F(H)$, where $F(H)$ usually has a power-law form. LaSb_2 is known to obey this rule, commonly referred to as Kohler's rule, with $F(H) = H$ [12]. One can also make a similar analysis by substituting the the Hall resistance for the magnetic field H . The resulting modified Kohler plot for LaSb_2 is shown in the left inset of Fig. 3. The solid line in the plot has a slope of $d(\rho_{xy}/\rho_{xx})/dH = 2/3$ indicating that $\rho_{xy}/\rho_{xx} \propto H^{2/3}$. Interestingly, Ag_2Se also exhibits power-law behavior but with a low temperature modified Kohler slope of $d(\rho_{xy}/\rho_{xx})/dH = 5/3$ [8]. This suggests that the underlying MR mechanisms in these two seemingly unrelated systems may be similar and that the differing scaling exponents is a dimensionality effect.

In conclusion, we show that crystalline LaSb_2 is an attractive material for use as a high magnetic field sensor. It is relatively easy to synthesize, and electrical contact can be made with silver epoxy. By virtue of its highly anisotropic structure, LaSb_2 can be used in either a transverse MR configuration or a Hall configuration. The sensitivity in both configurations is quite good. Calibration curves for both the MR and the Hall resistance can be made using a fourth-order polynomial, thus avoiding numerical difficulties associated with complicated fitting forms.

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- [1] M. N. Baibich, J.M. Broto, A. Fert, F.N. Vandau, F. Petro, P. Etienne, G. Creuzet, A. Friederich, and J. Chazelas, *Phys. Rev. Lett.* 61, 2472 (1988); R.E. Camley and R.L. Stamps, *J. Phys. Cond. Matter* 5, 3727 (1993).
- [2] S. Jin, T.H. Tiefel, M. McCormack, R.A. Fastnacht, R. Ramesh, and L.H. Chen, *Science* 264, 413 (1994).
- [3] A.A. Abrikosov, *Phys. Rev. B* 60, 4231 (1999); A.A. Abrikosov, *Europhys. Lett.*, 49 (6), 789 (2000).
- [4] I.M. Lifshits and V.G. Peshanskii, *Sov. Phys. JETP*, 8, 875 (1959).
- [5] L.M. Falicov and H. Smith, *Phys. Rev. Lett.* 29, 124 (1972).
- [6] D.E. Soule, *Phys. Rev.* 112, 698 (1958); J.W. McClure and W.J. Spry, *Phys. Rev.* 165, 809 (1968).
- [7] In this case a multi-fold positive, linear, magnetoconductance is seen, V.Yu. Butko, J.F. Ditus, and P.W. Adams, *Phys. Rev. Lett.* 85, 162 (2000); V.Yu. Butko and P.W. Adams, *Nature* 409, 161 (2001).
- [8] A. Humann, J.B. Betts, G.S. Boebinger, A. Migliori, T.F. Rosenbaum, and L. Saboungi, *Nature* 417, 421 (2002).
- [9] R. Wang and H. Steinrück, *Inorg. Chem.* 6, 1685 (1967).
- [10] F. Hullinger, in *Handbook of Physics and Chemistry of Rare Earths*, edited by K.A. Gschneidner and L. Eyring (North-Holland, Amsterdam, 1979), Vol. 4, p. 153.
- [11] X-ray analysis determined the lattice constants to be 0.6319 nm, 0.6173 nm, and 1.857 nm for the a, b, and c crystallographic directions, respectively.
- [12] S.L. Bud'ko, P.C. Canfield, C.H. Mielke, and A.H. Lacerda, *Phys. Rev. B* 57, 13624 (1998).
- [13] P.C. Canfield and Z. Fisk, *Philos. Mag. B* 65, 1117 (1992).
- [14] Epoxy Technology, 14 Fortune Dr., Billerica, MA, 01821 (www.epotek.com).
- [15] M. Naito and S. Tanaka, *J. Phys. Soc. Jpn.* 51, 228 (1982).
- [16] A.H.C. Neto, *Phys. Rev. Lett.* 86, 4382 (2001).
- [17] J.A. Wilson, F.J. DiSalvo, and S.M. Mahajan, *Adv. Phys.* 24, 117 (1975).
- [18] N.W. Ashcroft and N.D. Mermin, *Solid State Physics* (Saunders, New York, 1976).
- [19] P.L. Kapitza, *Proc. R. Soc. London, Ser. A*, 119, 358 (1928).
- [20] H.L. Stormer, K.W. West, L.N. Pfeiffer, and K.W. West, *Solid State Comm.*, 84, 95 (1992).
- [21] A.W. Overhauser, *Phys. Rev. B* 3, 3173 (1971).
- [22] R.A. Young, *Phys. Rev.* 175, 813 (1968).
- [23] A.A. Abrikosov, *Fundamentals of the Theory of Metals* (North-Holland, Amsterdam, 1988).

Figures

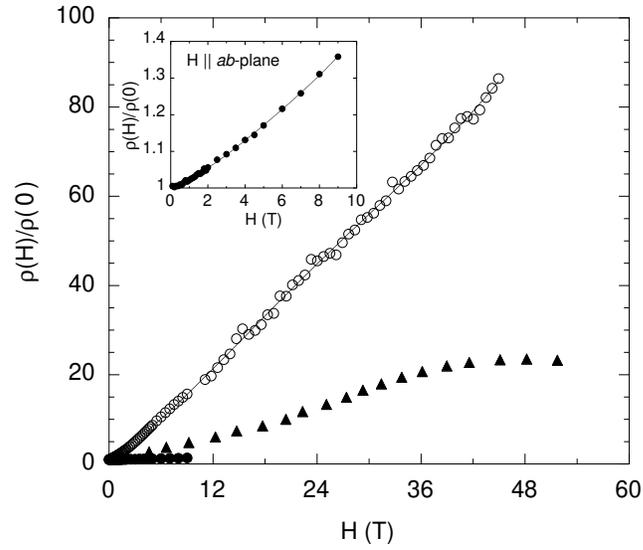


FIG. 1: Transverse MR of $LaSb_2$ at $T = 2$ K with the current in the ab -plane and magnetic field oriented parallel (closed circles) and perpendicular (open circles) to the ab -plane. The solid triangles represent the MR of Ag_2Se as taken from Ref. 8. Inset: Low field MR with $H \parallel ab$ -plane. The solid lines represent a least-squares fit to the data using a fourth-order polynomial (Table 1).

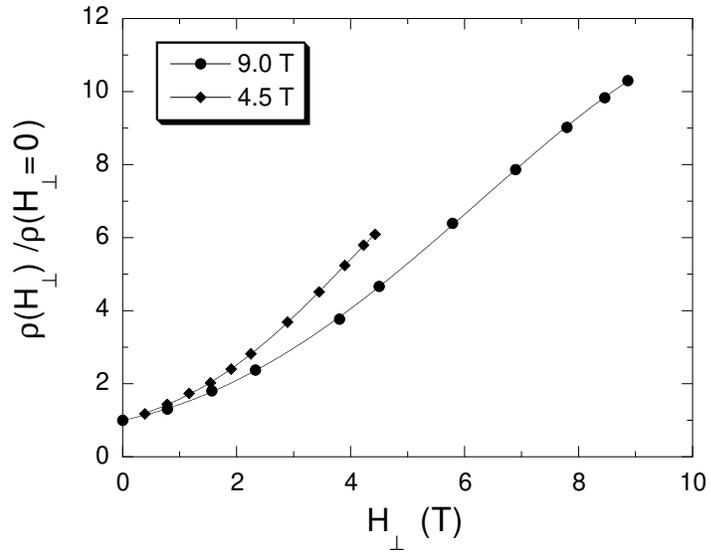


FIG. 2: MR in a tilted magnetic field. The samples were rotated out of the H k ab -plane in constant magnetic fields of 9.0 T and 4.5 T. The MR at 2 K is plotted as a function of the perpendicular component of the field. The solid lines represent a least-squares fit to the data using a fourth-order polynomial (Table 1).

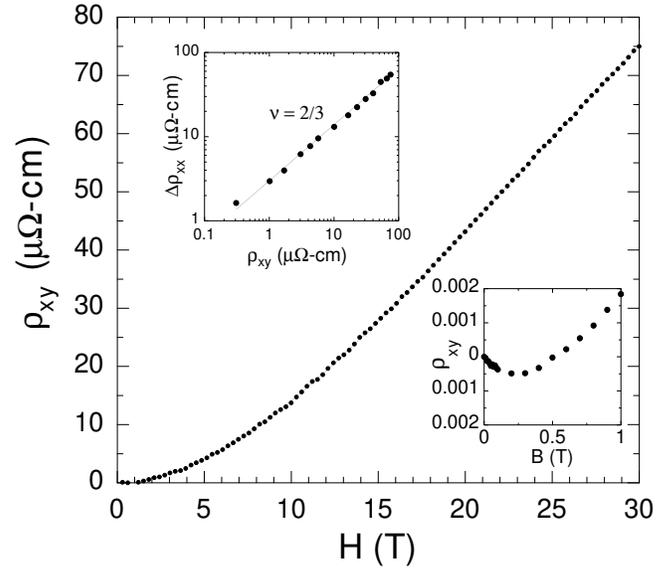


FIG. 3: Hall resistivity as a function of magnetic field at $T = 2$ K. The solid lines represent a least-squares fit to the data using a fourth-order polynomial (Table 1). Right inset: low field behavior of ρ_{xy} showing a crossover from electron-like to hole-like conduction with increasing field. Left inset: log-log plot of $\Delta\rho_{xx} = \rho_{xx}(H) - \rho_{xx}(0)$ as a function of the Hall resistivity at $T = 2$ K. The solid line has slope $\nu = 2/3$. The linearity of the data suggests that $\Delta\rho_{xx} \propto \rho_{xy}^{2/3}$.

Tables

TABLE I: Polynomial coefficients obtained from a least squares fit to the data in Figs. 1–3 using a fourth-order polynomial, $f(H) = a_0 + a_1H + a_2H^2 + a_3H^3 + a_4H^4$.

	0	1	2	3	4
$(H) = (0) (H = k \text{ } \text{C})$	1	1.236	0.0579	-1.874×10^{-3}	2.019×10^{-5}
$(H) = (0) (H = ? \text{ } \text{C})$	1	0.0182	5.601×10^{-3}	-6.260×10^{-4}	3.032×10^{-5}
$(H ?) = (0) (H = 9T)$	1	0.3315	0.1023	4.598×10^{-3}	-7.931×10^{-4}
$(H ?) = (0) (H = 4.5T)$	1	0.4624	0.0827	0.04644	-6.775×10^{-3}
$x_Y (H) (-\text{cm})$	0	0.0225	0.1781	-4.309×10^{-3}	3.757×10^{-5}